Nguyen Tien Son

List of Publications by Year
in descending order

232 papers	7,904 citations	44066 48 h-index	64791 79 g-index
238 all docs	238 docs citations	238 times ranked	3780 citing authors

#	Article	IF	Citations
1	Fabrication and nanophotonic waveguide integration of silicon carbide colour centres with preserved spin-optical coherence. Nature Materials, 2022, 21, 67-73.	27.5	80
2	Broadband single-mode planar waveguides in monolithic 4H-SiC. Journal of Applied Physics, 2022, 131, 025703.	2.5	1
3	Five-second coherence of a single spin with single-shot readout in silicon carbide. Science Advances, 2022, 8, eabm5912.	10.3	57
4	Electromagnetically induced transparency in inhomogeneously broadened divacancy defect ensembles in SiC. Journal of Applied Physics, 2022, 131, 094401.	2.5	1
5	Fluorescence spectrum and charge state control of divacancy qubits via illumination at elevated temperatures in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>4</mml:mn><mml:mi>H</mml:mi></mml:mrow></mm silicon carbide. Physical Review B, 2022, 105, .	3.2	5
6	Spin-Optical Dynamics and Quantum Efficiency of a Single V1 Center in Silicon Carbide. Physical Review Applied, 2022, 17, .	3.8	5
7	Modified divacancies in 4H-SiC. Journal of Applied Physics, 2022, 132, .	2.5	3
8	Narrow inhomogeneous distribution of spin-active emitters in silicon carbide. Applied Physics Letters, 2021, 118, .	3.3	13
9	Charge state control of the silicon vacancy and divacancy in silicon carbide. Journal of Applied Physics, 2021, 129, .	2.5	16
10	Towards identification of silicon vacancy-related electron paramagnetic resonance centers in 4H -SiC. Physical Review B, 2021, 104, .	3.2	9
11	Deep levels related to the carbon antisiteâ€“vacancy pair in 4H-SiC. Journal of Applied Physics, 2021, 130, .	2.5	5
12	Nanofabricated and Integrated Colour Centres in Silicon Carbide with High-Coherence Spin-Optical Properties. , 2021, , .		0
13	Dipolar spin relaxation of divacancy qubits in silicon carbide. Npj Computational Materials, 2021, 7, .	8.7	7
14	Spectrally reconfigurable quantum emitters enabled by optimized fast modulation. Npj Quantum Information, 2020, 6, .	6.7	38
15	Electron paramagnetic resonance and theoretical study of gallium vacancy in <i>Î²</i> -Ga2O3. Applied Physics Letters, 2020, 117, .	3.3	33
16	Entanglement and control of single nuclear spins in isotopically engineered silicon carbide. Nature Materials, 2020, 19, 1319-1325.	27.5	98
17	Vibronic States and Their Effect on the Temperature and Strain Dependence of Silicon-Vacancy Qubits in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mn>4</mml:mn><mml:mi>H</mml:mi></mml:math>-<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mrow><mml:mi>Si</mml:mi><mml:mi mathvariant="normal">C</mml:mi></mml:mrow></mml:math>. Physical Review Applied, 2020, 13, .	3.8	47
18	Developing silicon carbide for quantum spintronics. Applied Physics Letters, 2020, 116, .	3.3	101

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19	Spin-controlled generation of indistinguishable and distinguishable photons from silicon vacancy centres in silicon carbide. Nature Communications, 2020, 11, 2516.	12.8	56
20	Spin-relaxation times exceeding seconds for color centers with strong spinâ€“orbit coupling in SiC. New Journal of Physics, 2020, 22, 103051.	2.9	15
21	Static and Dynamic Stark Tuning of the Silicon Vacancy in Silicon Carbide. , 2020, , .		0
22	Optical Properties of Vanadium in 4 <i>H</i> Silicon Carbide for Quantum Technology. Physical Review Applied, 2019, 12, .	3.8	51
23	Electrical Charge State Manipulation of Single Silicon Vacancies in a Silicon Carbide Quantum Optoelectronic Device. Nano Letters, 2019, 19, 7173-7180.	9.1	61
24	Energy levels and charge state control of the carbon antisite-vacancy defect in 4H-SiC. Applied Physics Letters, 2019, 114, .	3.3	17
25	High-fidelity spin and optical control of single silicon-vacancy centres in silicon carbide. Nature Communications, 2019, 10, 1954.	12.8	167
26	Identification of divacancy and silicon vacancy qubits in 6H-SiC. Applied Physics Letters, 2019, 114, 112107.	3.3	28
27	Ligand hyperfine interactions at silicon vacancies in 4H-SiC. Journal of Physics Condensed Matter, 2019, 31, 195501.	1.8	13
28	First-Principles Study on Photoluminescence Quenching of Divacancy in 4H SiC. Materials Science Forum, 2019, 963, 714-717.	0.3	1
29	Electrical and optical control of single spins integrated in scalable semiconductor devices. Science, 2019, 366, 1225-1230.	12.6	157
30	Stabilization of point-defect spin qubits by quantum wells. Nature Communications, 2019, 10, 5607.	12.8	42
31	Coherent electrical readout of defect spins in silicon carbide by photo-ionization at ambient conditions. Nature Communications, 2019, 10, 5569.	12.8	43
32	First principles predictions of magneto-optical data for semiconductor point defect identification: the case of divacancy defects in 4Hâ€“SiC. New Journal of Physics, 2018, 20, 023035.	2.9	39
33	Quantum Properties of Dichroic Silicon Vacancies in Silicon Carbide. Physical Review Applied, 2018, 9, .	3.8	90
34	Excitation properties of the divacancy in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>4</mml:mn><mml:mi>H</mml:mi></mml:mrow></mml: -SiC. Physical Review B, 2018, 98, .	3.2	44
35	Identification and tunable optical coherent control of transition-metal spins in silicon carbide. Npj Quantum Information, 2018, 4, .	6.7	53
36	Bright single photon sources in lateral silicon carbide light emitting diodes. Applied Physics Letters, 2018, 112, .	3.3	33

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37	Scalable Quantum Photonics with Single Color Centers in Silicon Carbide. Nano Letters, 2017, 17, 1782-1786.	9.1	129
38	Resonant optical spectroscopy and coherent control of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi mathvariant="normal">C</mml:mi><mml:msup><mml:mrow><mml:mi mathvariant="normal">r</mml:mi></mml:mrow><mml:mrow><mml:mn>4</mml:mn><mml:mo>+</mml:mo></mml:mrow></mml:msup ensembles in SiC and GaN. Physical Review B, 2017, 95, .	3.2	59
39	Identification of Si-vacancy related room-temperature qubits in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>4</mml:mn><mml:mi>H</mml:mi></mml:mrow></mm silicon carbide. Physical Review B, 2017, 96, .	3.2	74
40	Isolated Spin Qubits in SiC with a High-Fidelity Infrared Spin-to-Photon Interface. Physical Review X, 2017, 7, .	8.9	125
41	Stark tuning and electrical charge state control of single divacancies in silicon carbide. Applied Physics Letters, 2017, 111, .	3.3	62
42	Scalable Quantum Photonics with Single Color Centers in Silicon Carbide. , 2017, , .		2
43	Electronic properties of defects in highâ€fluence electronâ€irradiated bulk GaN. Physica Status Solidi (B): Basic Research, 2016, 253, 521-526.	1.5	3
44	Electronic properties of Si-doped Al<i>x</i>Ga1â^'xN with aluminum mole fractions above 80%. Journal of Applied Physics, 2016, 120, .	2.5	47
45	Deep levels in as-grown and electron-irradiated n-type GaN studied by deep level transient spectroscopy and minority carrier transient spectroscopy. Journal of Applied Physics, 2016, 119, .	2.5	8
46	Donor and double-donor transitions of the carbon vacancy related EH6â^•7 deep level in 4H-SiC. Journal of Applied Physics, 2016, 119, .	2.5	16
47	Electronic properties of the residual donor in unintentionally doped Î²-Ga2O3. Journal of Applied Physics, 2016, 120, .	2.5	68
48	n-Type conductivity bound by the growth temperature: the case of Al_{0.72}Ga_{0.28}N highly doped by silicon. Journal of Materials Chemistry C, 2016, 4, 8291-8296.	5.5	8
49	Vector Magnetometry Using Silicon Vacancies in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mn>4</mml:mn><mml:mi>H</mml:mi></mml:math>-SiC Under Ambient Conditions. Physical Review Applied, 2016, 6, .	3.8	66
50	Optical properties and Zeeman spectroscopy of niobium in silicon carbide. Physical Review B, 2015, 92, .	3.2	6
51	Exciton luminescence in AlN triggered by hydrogen and thermal annealing. Applied Physics Letters, 2015, 106, .	3.3	11
52	Shallow donor in natural MoS2. Physica Status Solidi - Rapid Research Letters, 2015, 9, 707-710.	2.4	5
53	On the behavior of silicon donor in conductive Al<i>_x</i>Ga_{1â€"<i>x</i>}N (0.63) Tj ETQq1 1 0.784314 rgBT /	1.5	8
54	Conjugated Polyelectrolyte Blends for Electrochromic and Electrochemical Transistor Devices. Chemistry of Materials, 2015, 27, 6385-6393.	6.7	83

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55	Isolated electron spins in silicon carbide with millisecond coherence times. Nature Materials, 2015, 14, 160-163.	27.5	362
56	Coherent control of single spins in silicon carbide at room temperature. Nature Materials, 2015, 14, 164-168.	27.5	472
57	Hydrogen at zinc vacancy of ZnO: An EPR and ESEEM study. , 2014, , .		4
58	Quantitative comparison between Z1â^•2 center and carbon vacancy in 4H-SiC. Journal of Applied Physics, 2014, 115, .	2.5	39
59	Stable and metastable Si negative-U centers in AlGaN and AlN. Applied Physics Letters, 2014, 105, .	3.3	47
60	Radiation-induced defects in GaN bulk grown by halide vapor phase epitaxy. Applied Physics Letters, 2014, 105, .	3.3	21
61	Characterization of the nitrogen split interstitial defect in wurtzite aluminum nitride using density functional theory. Journal of Applied Physics, 2014, 116, .	2.5	9
62	Theoretical and electron paramagnetic resonance studies of hyperfine interaction in nitrogen doped 4H and 6H SiC. Journal of Applied Physics, 2014, 115, .	2.5	17
63	Electronic Defects in Electron-Irradiated Silicon Carbide and III-Nitrides. , 2014, , 417-451.		0
64	Negative-<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>U</mml:mi></mml:math>carbon vacancy in 4<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>H</mml:mi></mml:math>-SiC: Assessment of charge correction schemes and identification of the negative carbon vacancy at the quasicubic site. Physical Review B, 2013, 88, .	3.2	45
65	Negative-U behavior of the Si donor in Al0.77Ga0.23N. Applied Physics Letters, 2013, 103, 042101.	3.3	9
66	Electron Paramagnetic Resonance Studies of Nb in 6H-SiC. Materials Science Forum, 2013, 740-742, 385-388.	0.3	0
67	Magnetic resonance identification of hydrogen at a zinc vacancy in ZnO. Journal of Physics Condensed Matter, 2013, 25, 335804.	1.8	13
68	The complex impact of silicon and oxygen on the n-type conductivity of high-Al-content AlGaN. Applied Physics Letters, 2013, 102, .	3.3	30
69	Investigation on origin of Z1/2 center in SiC by deep level transient spectroscopy and electron paramagnetic resonance. Applied Physics Letters, 2013, 102, .	3.3	56
70	Electronic Configuration of Tungsten in 4H-, 6H-, and 15R-SiC. Materials Science Forum, 2012, 717-720, 211-216.	0.3	0
71	Electron paramagnetic resonance and theoretical studies of Nb in 4H- and 6H-SiC. Journal of Applied Physics, 2012, 112, .	2.5	11
72	Transition Metal Defects in Cubic and Hexagonal Polytypes of SiC: Site Selection, Magnetic and Optical Properties from <i>Ab Initio</i> Calculations. Materials Science Forum, 2012, 717-720, 205-210.	0.3	2

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73	Negative-<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>U</mml:mi></mml:math>System of Carbon Vacancy in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mn>4</mml:mn><mml:mi>H</mml:mi></mml:math>-SiC. Physical Review Letters, 2012, 109, 187603.	7.8	219
74	Optical identification and electronic configuration of tungsten in 4H- and 6H-SiC. Physica B: Condensed Matter, 2012, 407, 1462-1466.	2.7	14
75	Asymmetric Split-Vacancy Defects in SiC Polytypes: A Combined Theoretical and Electron Spin Resonance Study. Physical Review Letters, 2011, 107, 195501.	7.8	22
76	Silicon in AlN: shallow donor and DX behaviors. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2167-2169.	0.8	7
77	Defects at nitrogen site in electron-irradiated AlN. Applied Physics Letters, 2011, 98, .	3.3	10
78	Shallow donor and DX states of Si in AlN. Applied Physics Letters, 2011, 98, .	3.3	49
79	Radiation-induced defects in GaN. Physica Scripta, 2010, T141, 014015.	2.5	6
80	The EI4 EPR centre in 6H SiC. Physica Scripta, 2010, T141, 014013.	2.5	0
81	EPR and ENDOR Studies of Shallow Donors in SiC. Applied Magnetic Resonance, 2010, 39, 49-85.	1.2	14
82	Magnetic characterization of conductance electrons in GaN. Physica Status Solidi (B): Basic Research, 2010, 247, 1728-1731.	1.5	5
83	The Carbon Vacancy Related EI4 Defect in 4H-SiC. Materials Science Forum, 2010, 645-648, 399-402.	0.3	1
84	Group-II acceptors in wurtzite AlN: A screened hybrid density functional study. Applied Physics Letters, 2010, 96, .	3.3	34
85	EPR and<i>ab initio</i>calculation study on the EI4 center in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mn>4</mml:mn><mml:mi>H</mml:mi></mml:mrow></mml:math>-and<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mn>6</mml:mn><mml:mi>H</mml:mi><mml:mtext>-SiC</mml:mtext></mml:mrow></mml:math>. Physical Review B, 2010, 82, .	3.2	12
86	Identification of the gallium vacancyâ€“oxygen pair defect in GaN. Physical Review B, 2009, 80, .	3.2	43
87	Defects Introduced by Electron-Irradiation at Low Temperatures in SiC. Materials Science Forum, 2009, 615-617, 377-380.	0.3	2
88	Photo-EPR Studies on Low-Energy Electron-Irradiated 4H-SiC. Materials Science Forum, 2009, 615-617, 401-404.	0.3	0
89	The silicon vacancy in SiC. Physica B: Condensed Matter, 2009, 404, 4354-4358.	2.7	91
90	Deep levels in lowâ€energy electronâ€irradiated 4Hâ€SiC. Physica Status Solidi - Rapid Research Letters, 2009, 3, 121-123.	2.4	10

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91	Identification of a Frenkel-pair defect in electron-irradiated 3<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>C</mml:mi></mml:mrow></mml:math>SiC. Physical Review B, 2009, 80, .	3.2	10
92	Water adsorption on fullerene-like carbon nitride overcoats. Thin Solid Films, 2008, 517, 1106-1110.	1.8	40
93	EPR identification of intrinsic defects in SiC. Physica Status Solidi (B): Basic Research, 2008, 245, 1298-1314.	1.5	60
94	Common point defects in as-grown ZnO substrates studied by optical detection of magnetic resonance. Journal of Crystal Growth, 2008, 310, 1006-1009.	1.5	4
95	Intrinsic Defects in HPSI 6H-SiC: an EPR Study. Materials Science Forum, 2008, 600-603, 381-384.	0.3	4
96	New Type of Defects Explored by Theory: Silicon Interstitial Clusters in SiC. Materials Science Forum, 2008, 600-603, 413-416.	0.3	0
97	EPR Identification of Defects and Impurities in SiC: To be Decisive. Materials Science Forum, 2008, 600-603, 279-284.	0.3	2
98	Electron paramagnetic resonance study on n-type electron-irradiated 3C-SiC. Journal of Physics: Conference Series, 2008, 100, 042032.	0.4	0
99	Theoretical study of small silicon clusters in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mn>4</mml:mn><mml:mi>H</mml:mi><mml:mtext>âˆ’</mml:mtext><mml:mi mathvariant="normal">Si</mml:mi><mml:mi mathvariant="normal">C</mml:mi></mml:mrow></mml:math>. Physical Review B, 2007, 76, .	3.2	16
100	Deep levels and carrier compensation in V-doped semi-insulating 4H-SiC. Applied Physics Letters, 2007, 91, 202111.	3.3	10
101	Recombination centers in as-grown and electron-irradiated ZnO substrates. Journal of Applied Physics, 2007, 102, 093504.	2.5	18
102	Influence of Cooling Rate after High Temperature Annealing on Deep Levels in High-Purity Semi-Insulating 4H-SiC. Materials Science Forum, 2007, 556-557, 371-374.	0.3	2
103	A Theoretical Study on Aluminium-Related Defects in SiC. Materials Science Forum, 2007, 556-557, 445-448.	0.3	3
104	Deep Acceptor Levels of the Carbon Vacancy-Carbon Antisite Pairs in 4H-SiC. Materials Science Forum, 2007, 556-557, 449-452.	0.3	4
105	Intrinsic Defects in Semi-Insulating SiC: Deep Levels and their Roles in Carrier Compensation. Materials Science Forum, 2007, 556-557, 465-468.	0.3	4
106	Ab initiosupercell calculations on aluminum-related defects in SiC. Physical Review B, 2007, 75, .	3.2	24
107	Defects and carrier compensation in semi-insulating4Hâˆ’SiCsubstrates. Physical Review B, 2007, 75, .	3.2	60
108	Prominent defects in semi-insulating SiC substrates. Physica B: Condensed Matter, 2007, 401-402, 67-72.	2.7	17

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109	Magnetic resonance studies of defects in electron-irradiated ZnO substrates. Physica B: Condensed Matter, 2007, 401-402, 507-510.	2.7	2
110	Clustering of vacancy defects in high-purity semi-insulating SiC. Physical Review B, 2007, 75, .	3.2	30
111	Electron paramagnetic resonance and theoretical studies of shallow phosphorous centers in3C-,4H-, and6Hâ^'SiC. Physical Review B, 2006, 73, .	3.2	31
112	Electrical characterization of metastable carbon clusters inSiC: A theoretical study. Physical Review B, 2006, 73, .	3.2	38
113	Intrinsic defects in high-purity SiC. Microelectronic Engineering, 2006, 83, 130-134.	2.4	18
114	Pulsed EPR studies of Phosphorus shallow donors in diamond and SiC. Physica B: Condensed Matter, 2006, 376-377, 358-361.	2.7	13
115	Identification of the Carbon Antisite-Vacancy Pair in4H-SiC. Physical Review Letters, 2006, 96, 145501.	7.8	72
116	Divacancy in 4H-SiC. Physical Review Letters, 2006, 96, 055501.	7.8	172
117	Identification of divacancies in 4H-SiC. Physica B: Condensed Matter, 2006, 376-377, 334-337.	2.7	6
118	Optical and morphological features of bulk and homoepitaxial ZnO. Superlattices and Microstructures, 2006, 39, 247-256.	3.1	10
119	Divacancy Model for P6/P7 Centers in 4H- and 6H-SiC. Materials Science Forum, 2006, 527-529, 527-530.	0.3	6
120	Divacancy and Its Identification: Theory. Materials Science Forum, 2006, 527-529, 523-526.	0.3	11
121	Characterization of Semi-insulating SiC. Materials Research Society Symposia Proceedings, 2006, 911, 3.	0.1	4
122	Shallow P Donors in 3C-, 4H- and 6H-SiC. Materials Science Forum, 2006, 527-529, 593-596.	0.3	2
123	Electron Paramagnetic Resonance Study of the HEI4/SI5 Center in 4H-SiC. Materials Science Forum, 2006, 527-529, 543-546.	0.3	7
124	Optical Studies of Deep Centers in Semi-Insulating SiC. Materials Science Forum, 2006, 527-529, 455-460.	0.3	2
125	Signature of the Negative Carbon Vacancy-Antisite Complex. Materials Science Forum, 2006, 527-529, 539-542.	0.3	4
126	Electron Paramagnetic Resonance of Shallow Phosphorous Centers in 4H- and 6H-SiC. Materials Science Forum, 2005, 483-485, 515-518.	0.3	5

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127	Theoretical Investigations of Complexes of p-Type Dopants and Carbon Interstitial in SiC: Bistable, Negative-U Defects. Materials Science Forum, 2005, 483-485, 519-522.	0.3	5
128	Activation of shallow boron acceptor in Câˆ•B coimplanted silicon carbide: A theoretical study. Applied Physics Letters, 2005, 86, 102108.	3.3	17
129	Possibility for the electrical activation of the carbon antisite by hydrogen inSiC. Physical Review B, 2005, 71, .	3.2	9
130	EPR and theoretical studies of negatively charged carbon vacancy in4Hâ^'SiC. Physical Review B, 2005, 71, .	3.2	55
131	Hyperfine Interaction of Nitrogen Donor in 4H-SiC Studied by Pulsed-ENDOR. Materials Science Forum, 2005, 483-485, 351-354.	0.3	2
132	Diffusion of hydrogen in perfect,p-type doped, and radiation-damaged4Hâ^'SiC. Physical Review B, 2004, 69, .	3.2	18
133	Annealing behavior of the carbon vacancy in electron-irradiated 4H-SiC. Journal of Applied Physics, 2004, 96, 2406-2408.	2.5	42
134	Hyperfine interaction of the nitrogen donor in4Hâ^'SiC. Physical Review B, 2004, 70, .	3.2	12
135	Annealing Behaviour of Vacancy-and Antisite-Related Defects in Electron-Irradiated 4H-SiC. Materials Science Forum, 2004, 457-460, 473-476.	0.3	9
136	Antisites as Possible Origin of Irradiation Induced Photoluminescence Centers in SiC: A Theoretical Study on Clusters of Antisites and Carbon Interstitials in 4H-SiC. Materials Science Forum, 2004, 457-460, 443-448.	0.3	1
137	EPR and theoretical studies of positively charged carbon vacancy in 4H-SiC. Physical Review B, 2004, 70, .	3.2	50
138	Defects in High-Purity Semi-Insulating SiC. Materials Science Forum, 2004, 457-460, 437-442.	0.3	57
139	Electronic Structure of Deep Defects in SiC. Advanced Texts in Physics, 2004, , 461-492.	0.5	7
140	Cyclotron Resonance Studies of Effective Masses and Band Structure in SiC. Advanced Texts in Physics, 2004, , 437-460.	0.5	7
141	Defects in SiC. Physica B: Condensed Matter, 2003, 340-342, 15-24.	2.7	22
142	Anti-site pair in SiC: a model of the DI center. Physica B: Condensed Matter, 2003, 340-342, 175-179.	2.7	7
143	HTCVD Grown Semi-Insulating SiC Substrates. Materials Science Forum, 2003, 433-436, 33-38.	0.3	52
144	Correlation between the antisite pair and theDIcenter in SiC. Physical Review B, 2003, 67, .	3.2	72

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145	Hydrogen passivation of nitrogen in SiC. Applied Physics Letters, 2003, 83, 1385-1387.	3.3	16
146	Defects in Semi-Insulating SiC Substrates. Materials Science Forum, 2003, 433-436, 45-50.	0.3	30
147	Calculation of Hyperfine Constants of Defects in 4H-SiC. Materials Science Forum, 2003, 433-436, 511-514.	0.3	18
148	Electrically active defects inn-type 4Hâ€"silicon carbide grown in a vertical hot-wall reactor. Journal of Applied Physics, 2003, 93, 4708-4714.	2.5	169
149	Silicon vacancy relatedTV2acenter in 4H-SiC. Physical Review B, 2003, 68, .	3.2	17
150	Aggregation of carbon interstitials in silicon carbide: A theoretical study. Physical Review B, 2003, 68, .	3.2	103
151	Metastable defects in 6Hâ€"SiC: experiments and modeling. Journal of Applied Physics, 2002, 91, 1324-1330.	2.5	19
152	Photoexcitation-electron-paramagnetic-resonance studies of the carbon vacancy in 4H-SiC. Applied Physics Letters, 2002, 81, 3945-3947.	3.3	70
153	Hole effective masses in 6H-SiC from optically detected cyclotron resonance. Physical Review B, 2002, 66, .	3.2	13
154	Ligand hyperfine interaction at the neutral silicon vacancy in 4H- and6Hâ^'SiC. Physical Review B, 2002, 66, .	3.2	43
155	Hole and Electron Effective Masses in 6H-SiC Studied by Optically Detected Cyclotron Resonance. Materials Science Forum, 2002, 389-393, 525-528.	0.3	2
156	Impurity-Controlled Dopant Activation - The Role of Hydrogen in p-Type Doping of SiC. Materials Science Forum, 2002, 389-393, 561-564.	0.3	5
157	The Neutral Silicon Vacancy in SiC: Ligand Hyperfine Interaction. Materials Science Forum, 2002, 389-393, 501-504.	0.3	8
158	Theoretical Investigation of an Intrinsic Defect in SiC. Materials Science Forum, 2002, 389-393, 477-480.	0.3	8
159	Ab initiodensity-functional supercell calculations of hydrogen defects in cubic SiC. Physical Review B, 2001, 63, .	3.2	109
160	Silicon Antisite in4HSiC. Physical Review Letters, 2001, 87, 045502.	7.8	35
161	Passivation of p-type dopants in 4H-SiC by hydrogen. Physica B: Condensed Matter, 2001, 308-310, 722-725.	2.7	14
162	As-Grown and Process-Induced Intrinsic Deep-Level Luminescence in 4H-SiC. Materials Science Forum, 2001, 353-356, 365-368.	0.3	6

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163	Boron Centers in 4H-SiC. Materials Science Forum, 2001, 353-356, 455-458.	0.3	24
164	Carbon vacancy-related defect in 4Hand 6HSiC. Physical Review B, 2001, 63, .	3.2	98
165	Impurity-controlled dopant activation: Hydrogen-determined site selection of boron in silicon carbide. Applied Physics Letters, 2001, 79, 2746-2748.	3.3	27
166	Intrinsic Defects in Silicon Carbide Polytypes. Materials Science Forum, 2001, 353-356, 499-504.	0.3	41
167	The Carbon Vacancy Pair in 4H and 6H SiC. Materials Science Forum, 2000, 338-342, 821-824.	0.3	6
168	Fast SiC Epitaxial Growth in a Chimney CVD Reactor and HTCVD Crystal Growth Developments. Materials Science Forum, 2000, 338-342, 131-136.	0.3	33
169	Silicon vacancy related defect in 4H and 6H SiC. Physical Review B, 2000, 61, 2613-2620.	3.2	223
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